

N-channel 120 V 6.7 mΩ standard level MOSFET in I2PAK 8 May 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic power supply equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive
- I2PAK package for slimline adaptors & height constrained applications

3. Applications

- AC-to-DC power supply
- Synchronous rectification
- Motor control
- Slimline adaptors & chargers

4. Quick reference data

| Table 1. Q | uick reference data | | | | | | |
|----------------------|---|--|---|-----|-------|-----|------|
| Symbol | Parameter | Conditions | r | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 120 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> | | - | - | 70 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 405 | W |
| Static chara | octeristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12 | | 4 | 5.7 | 6.7 | mΩ |
| Dynamic ch | aracteristics | | | | _ | | |
| Q _{GD} | gate-drain charge | V_{GS} = 10 V; I _D = 25 A; V _{DS} = 60 V; | | - | 61.9 | - | nC |
| Q _{G(tot)} | total gate charge | <u>Fig. 14; Fig. 15</u> | | - | 207.1 | - | nC |
| Avalanche r | ruggedness | · | | | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $\label{eq:VGS} \begin{split} V_{GS} &= 10 \text{ V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{I}_{D} = 70 \text{ A}; \\ V_{sup} &\leq 120 \text{ V}; \text{ unclamped}; \text{R}_{GS} = 50 \Omega; \\ \hline \text{Fig. 3} \end{split}$ | | - | - | 532 | mJ |

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5. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-------------|-------------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | mb | D |
| 2 | D | drain | | |
| 3 | S | source | | G L F A |
| mb | D | drain | 1 2 3 12PAK (SOT226) | mbb076 S |

6. Ordering information

| Table 3. Ordering information | | | | | | | |
|-------------------------------|---------|--|---------|--|--|--|--|
| Type number | Package | | | | | | |
| | Name | Description | Version | | | | |
| PSMN6R3-120ES | I2PAK | plastic single-ended package (I2PAK); TO-262 | SOT226 | | | | |

7. Limiting values

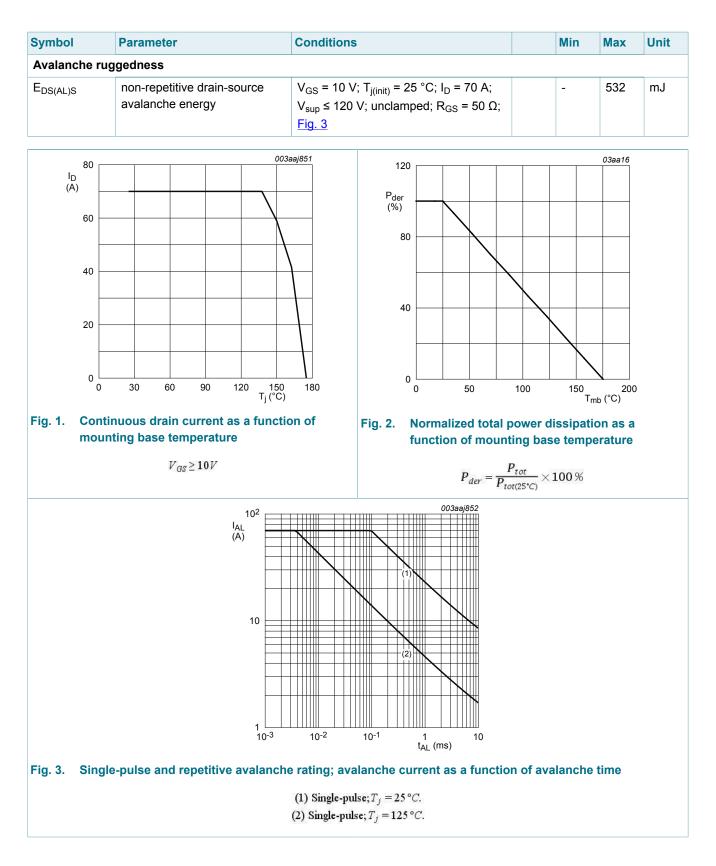
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|----------------------------|--|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 120 | V |
| V _{DGR} | drain-gate voltage | T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ | - | 120 | V |
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u> | - | 70 | А |
| | | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u> | - | 70 | А |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 4 | - | 280 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | - | 405 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | - | 260 | °C |
| Source-dra | in diode | | · | | |
| I _S | source current | T _{mb} = 25 °C | - | 70 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | - | 280 | А |

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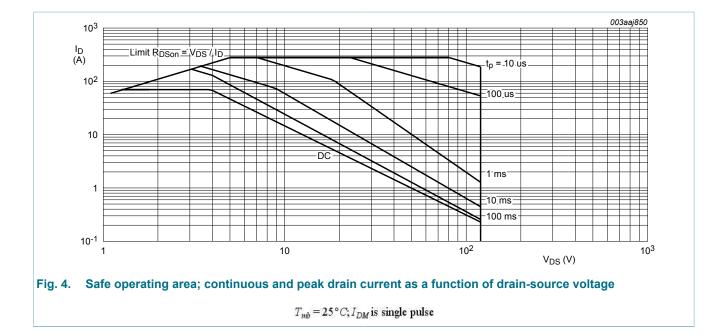
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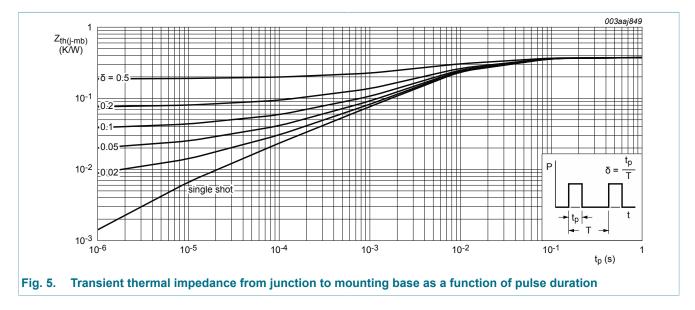
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8. Thermal characteristics

| Table 5. Thermal characteristics | | | | | | | | |
|----------------------------------|---|----------------------|--|-----|-----|------|------|--|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. <u>5</u> | | - | 0.3 | 0.37 | K/W | |
| R _{th(j-a)} | thermal resistance from junction to ambient | vertical in free air | | - | 65 | - | K/W | |



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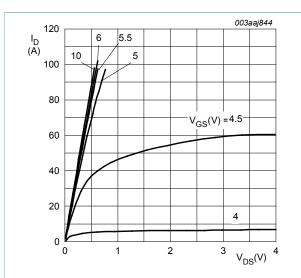
9. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---------------------------------------|---|------|-------|------|------|
| Static chara | octeristics | | | | | |
| V _{(BR)DSS} | drain-source | I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C | 120 | - | - | V |
| | breakdown voltage | I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C | 108 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10; Fig. 11 | 2 | 3 | 4 | V |
| | | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10; Fig. 11 | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10; Fig. 11 | - | - | 4.6 | V |
| I _{DSS} | drain leakage current | V_{DS} = 120 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.1 | 1 | μA |
| | | V _{DS} = 120 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 500 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | 10 | 100 | nA |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | 10 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12 | 4 | 5.7 | 6.7 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 13; Fig. 12 | - | 16.5 | 19.4 | mΩ |
| R _G | internal gate resistance (AC) | f = 1 MHz | 0.44 | 0.88 | 1.76 | Ω |
| Dynamic ch | aracteristics | · · · · · · · · · · · · · · · · · · · | I. | 1 | | _ |
| Q _{G(tot)} | total gate charge | I _D = 25 A; V _{DS} = 60 V; V _{GS} = 10 V; | - | 207.1 | - | nC |
| Q _{GS} | gate-source charge | Fig. 14; Fig. 15 | - | 43.2 | - | nC |
| Q _{GS(th)} | pre-threshold gate- source charge | | - | 29.8 | - | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate- source charge | | - | 13.4 | - | nC |
| Q _{GD} | gate-drain charge | | - | 61.9 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | I _D = 25 A; V _{DS} = 60 V; <u>Fig. 14; Fig. 15</u> | - | 4.3 | - | V |
| C _{iss} | input capacitance | V _{DS} = 60 V; V _{GS} = 0 V; f = 1 MHz; | - | 11384 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 16</u> | - | 534 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 358 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 60 V; R _L = 2.4 Ω; V _{GS} = 10 V; | - | 42.1 | - | ns |
| t _r | rise time | R _{G(ext)} = 5 Ω; T _j = 25 °C | - | 58.2 | - | ns |

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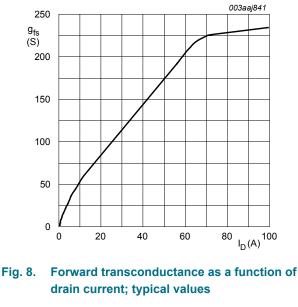
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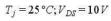
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | |
|---------------------|-----------------------|---|--|-----|-------|-----|------|--|
| t _{d(off)} | turn-off delay time | | | - | 142.1 | - | ns | |
| t _f | fall time | _ | | - | 67.7 | - | ns | |
| Source-drain | Source-drain diode | | | | | | | |
| V _{SD} | source-drain voltage | I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u> | | - | 0.79 | 1.2 | V | |
| t _{rr} | reverse recovery time | I_{S} = 25 A; dI_{S}/dt = -100 A/µs; V_{GS} = 0 V; | | - | 76.1 | - | ns | |
| Q _r | recovered charge | V _{DS} = 60 V | | - | 264.2 | - | nC | |

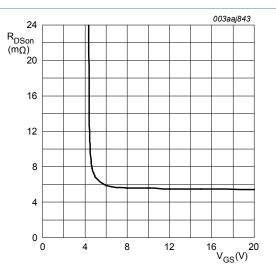




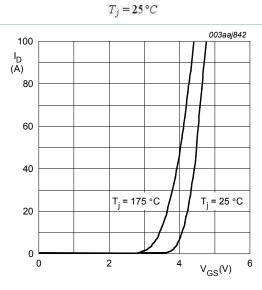










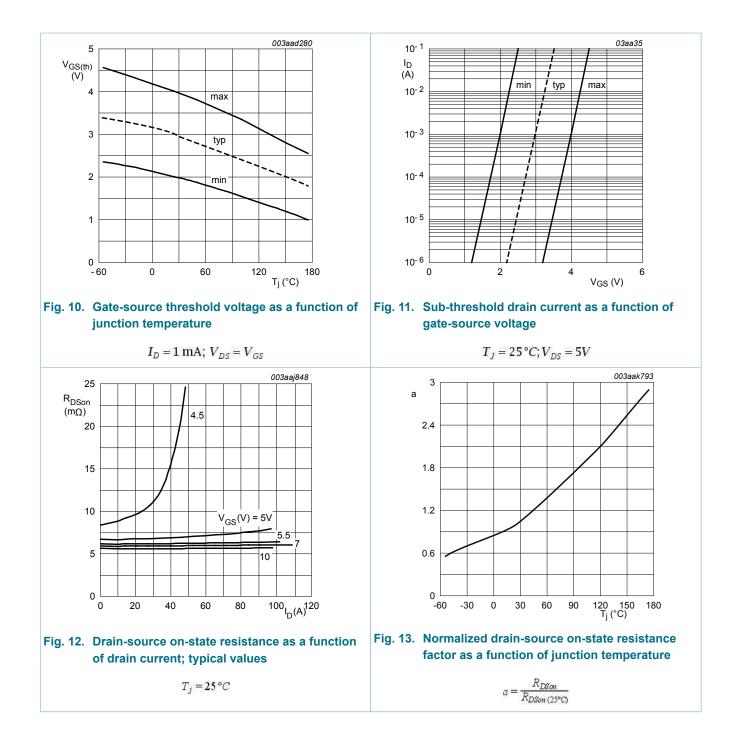




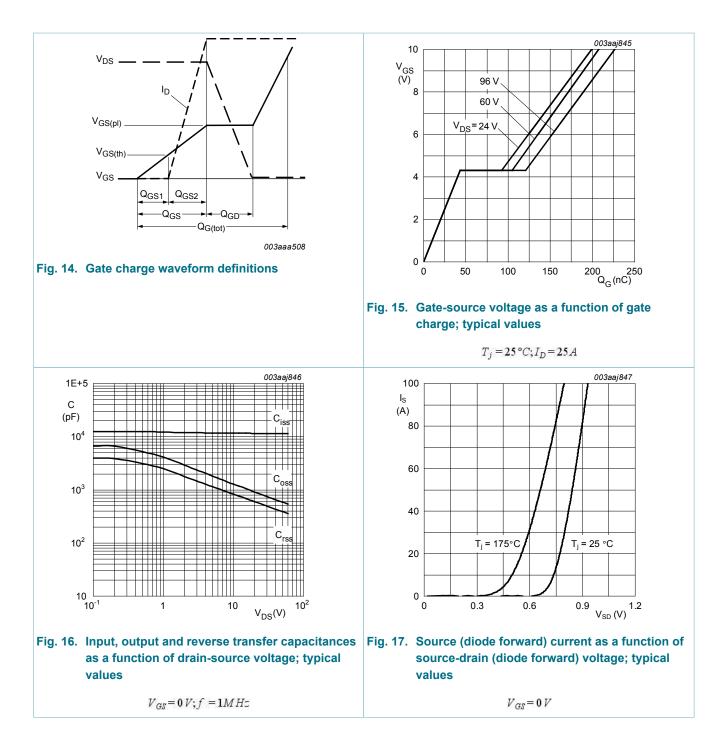
 $V_{DS} > I_D \times R_{DSon}$

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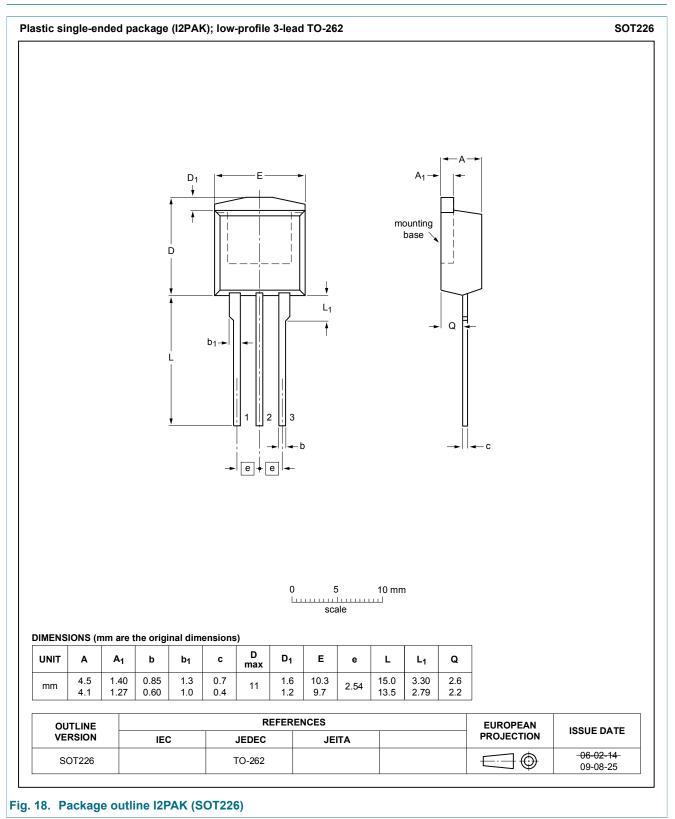


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10. Package outline



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11. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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